

AMENDMENTS TO THE CLAIMS:

1-11. (Canceled)

12. (Currently amended) An open system continuous atmospheric pressure chemical vapor deposition ~~production~~ apparatus of a film, comprising:

means for pre-heating a substrate;

means for heating ~~[[a]]~~ the pre-heated substrate ~~comprising silicon,~~

plural dispersion heads for discharging independently gaseous compounds for forming the film,

means for positioning a bottom end of a discharge port of a former dispersion head closer to a surface of the substrate than is a bottom end of discharge port of a latter dispersion head, and

means for conveying the heated ~~silicon~~ substrate, ~~heated to a predetermined temperature,~~ in a conveying direction from a position immediately below the discharge port of the former dispersion head to a position immediately below the discharge port of the latter dispersion head so that a film is formed on the substrate continuously in an open system by chemical vapor deposition under atmospheric pressure. ~~and~~

~~a partition for surrounding a discharged gas between the latter dispersion head and the silicon substrate, the partition being positioned below a circumference of bottom ends of the discharge port of the latter dispersion head.~~

13. (Canceled)

14. (Previously presented) The apparatus of claim 12, wherein said means for positioning and means for conveying cause a titanium oxide film to be formed in a non-uniform manner so that a concentration of the dopant element in the film varies through a thickness of the film so that the concentration of the dopant element in the titanium oxide film is higher adjacent a surface of the substrate than at a location spaced further away from the surface of the substrate.

15. (Currently amended) The apparatus of claim 12, wherein a difference between (i) a distance "A" from the bottom discharge end of the former dispersion head, and (ii) a distance "B" from the bottom discharge end of the latter dispersion head to the surface of the ~~silicon~~ substrate is from 0.1 to 30 mm.

16. (New) The apparatus of claim 12, further comprising means for a second pre-heating of the heated substrate after the film is deposited.

17. (New) The apparatus of claim 12, further comprising a partition for surrounding a discharged gas between the latter dispersion head and the substrate, the partition being positioned below a circumference of bottom end of the discharge port of the latter dispersion head.

18. (New) The apparatus of claim 17, wherein a bottom end of the partition is positioned below the bottom end of the discharge port of the latter dispersion head.

19. (New) The apparatus of claim 17, wherein an area of bottom end of the partition is greater than an area of the bottom end of the discharge port of the latter dispersion head.